

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claims 1-46 (Canceled)

Claim 47 (Previously presented): The semiconductor die of claim 67, wherein said tip structure is integrally formed with said one of the interconnection elements.

Claim 48 (Canceled)

Claim 49 (Previously presented): The semiconductor die of claim 67, wherein said one of the interconnection elements is resilient.

Claims 50-52 (Canceled)

Claim 53 (Previously presented): The semiconductor die of claim 67, wherein said tip structure comprises at least one of palladium, cobalt, rhodium, tungsten, or diamond.

Claim 54 (Previously presented): The semiconductor die of claim 67, wherein said tip structure comprises a material comprising a spring alloy.

Claim 55 (Previously presented): The semiconductor die of claim 67, wherein said tip structure is secured to said one of the interconnection elements by one of braze or solder.

Claims 56-59 (Canceled)

Claim 60 (Currently amended): A semiconductor die tested by making temporary electrical connections between interconnection elements of a contactor device and terminals of the die, the method of making the temporary electrical connections comprising:

moving at least one of the die or the contactor device such that terminals of the die are pressed against blades of interconnection elements of the contactor device and moved past first contact between the blades and the terminals, each blade comprising a cutting edge along a length of the blade,

the pressing of the terminals against the blades causing bodies of the interconnection elements to deflect away from the terminals, which causes the blades to wipe across the terminals in a motion that is within plus or minus forty-five degrees of an axis aligned with the length of the blade, the cutting edge of each blade slicing into a surface of each of the terminals so that a slice mark is created on each of the terminals.

Claim 61 (Previously presented): The semiconductor die of claim 60, wherein the motion of the blades across the terminals is within plus or minus thirty degrees of the axis.

Claim 62 (Previously presented): The semiconductor die of claim 60, wherein the motion of the blades across the terminals is approximately parallel to the axis.

Claim 63 (Previously presented): The semiconductor die of claim 60, wherein the blades slice through oxide layers formed on the terminals.

Claims 64-66 (Canceled)

Claim 67 (Previously presented): The semiconductor die of claim 60, wherein each of the blades composes a tip structure disposed on one of the interconnection elements.

Claims 68 and 69 (Canceled)

Claim 70 (Previously presented): The semiconductor die of claim 60, wherein each of the blades comprises tapered portions that form the cutting edge along the length of the blade.

Claim 71 (Previously presented): The semiconductor die of claim 60, wherein each of the blades comprises a base portion that is larger than the cutting edge of the blade, the blade further comprising tapered sidewalls that taper from the base portion to the cutting edge.

Claim 72 (Previously presented): The semiconductor die of claim 60, wherein the axis is coincident with the length of the blade.

Claim 73 (Previously presented): The semiconductor die of claim 60, wherein the slice mark created on each of the terminals corresponds to a portion of a shape of the corresponding blade that wipes across the terminal.

Claim 74 (Previously presented): The semiconductor die of claim 73, wherein the portion of the shape of the corresponding blade includes the cutting edge, which is formed by an intersection of inwardly sloping side walls of the corresponding blade.

Claim 75 (Previously presented): The semiconductor die of claim 73, wherein each blade comprises a first side wall and a second side wall, and wherein the first side wall slopes toward the second side wall and the second side wall slopes toward the first side wall such that the first side wall and the second side wall intersect to form the cutting edge of the blade, the portion of the shape of the corresponding blade comprising a portion of the first side wall, a portion of the second side wall, and at least a portion of the cutting edge.

Claim 76 (Previously presented): The semiconductor die of claim 73, wherein the shape of the corresponding blade comprises a triangular cross-sectional shape, a tip of the cross-sectional shape corresponding to the cutting edge, wherein the portion of the shape includes the tip of the triangular cross-sectional shape.

Claim 77 (Previously presented): The semiconductor die of claim 60, wherein the blades comprise palladium, rhodium, tungsten, or diamond.

Claim 78 (Previously presented): The semiconductor die of claim 60, wherein the blades comprise a first material and the terminals comprise a second material, and the first material is harder than the second material.

Claim 79 (New): The semiconductor die of claim 60, wherein the pressing of the terminals against the blades further causes an end of the blade to rotate away from the terminal.

Claim 80 (New): The semiconductor die of claim 79, wherein the end is a leading end of the blade.